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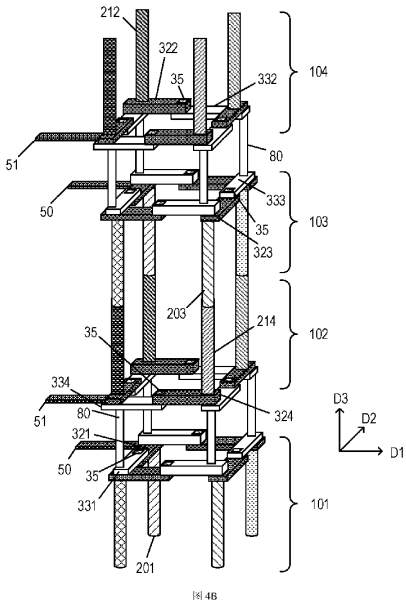
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(54) Title: SEMICONDUCTOR CHIP, SEMICONDUCTOR DEVICE AND FORMING METHOD THEREFOR

(54) 发明名称: 半导体芯片、半导体器件及其形成方法



(57) Abstract: The present disclosure relates to a semiconductor chip, a semiconductor device and a forming method therefor. The semiconductor chip comprises: a substrate comprising a top face and a bottom face; and a plurality of pairs of mutually independent signal through hole groups, wherein the signal through hole groups are arranged at intervals in the substrate, two signal through hole groups in each pair of signal through hole groups are symmetrically distributed with respect to an axis on the top face of the substrate and are respectively distributed in a first area and a second area on the two sides of the axis, the axis is parallel to a first direction or a second direction, each signal through hole group comprises a plurality of signal through holes arranged in a polygonal shape, any two signal through holes in each signal through hole group are electrically isolated, and each signal through hole penetrates the substrate in a third direction.

(57) 摘要: 本公开涉及一种半导体芯片、半导体器件及其形成方法。所述半导体芯片包括: 基底, 包括顶面和底面; 多对相互独立的信号通孔组, 各所述信号通孔组在基底中间隔排布, 且每对所述信号通孔组中的两个所述信号通孔组关于所述基底的顶面上的一条轴线对称分布, 且分别分布于所述轴线两侧的第一区域和第二区域, 所述轴线平行于第一方向或第二方向, 每个所述信号通孔组包括以多边形形状排布的多个信号通孔, 每个所述信号通孔组中任意两个所述信号通孔电性隔离, 每个所述信号通孔沿第三方向贯穿所述基底。

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CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN,
TD, TG)。

根据细则4.17的声明:

- 关于发明人身份(细则4.17(i))
- 关于申请人有权申请并被授予专利(细则4.17(ii))
- 关于申请人有权要求在先申请的优先权(细则4.17(iii))

本国际公布:

- 包括国际检索报告(条约第21条(3))。